SQJ980AEP

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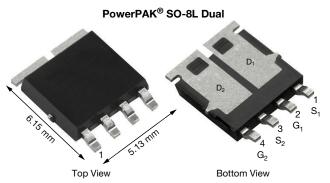
Vishay Siliconix

 D_2

S₂

N-Channel MOSFET

Automotive Dual N-Channel 75 V (D-S) 175 °C MOSFET



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FEATURES

- TrenchFET[®] Power MOSFET
- AEC-Q101 Qualified^d
- 100 % R_q and UIS Tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

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N-Channel MOSFET



RoHS COMPLIANT HALOGEN FREE

PRODUCT SUMMARY	
V _{DS} (V)	75
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.050
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.066
_D (A) per leg	8
Configuration	Dual

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ980AEP (for detailed order number please see <u>www.vishay.com/doc?79771</u>)

ABSOLUTE MAXIMUM RATINGS	$(T_C = 25 \ ^{\circ}C, \text{ unless})$	s otherwise noted	4)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	75	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current ^a	T _C = 25 °C		17	
Continuous Drain Current"	T _C = 125 °C	I _D	10	
Continuous Source Current (Diode Conduction	ı) ^a	I _S	30	А
Pulsed Drain Current ^b		I _{DM}	68	
Single Pulse Avalanche Current		I _{AS}	14	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	10	mJ
Mauianum Daura Diasia atia ab	T _C = 25 °C	P	34	10/
Maximum Power Dissipation ^b	$T_{\rm C} = 125 \ ^{\circ}{\rm C} \qquad \qquad P_{\rm D} \qquad \qquad 11$	W		
Operating Junction and Storage Temperature	Range	T _J , T _{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperate	ure) ^{e, f}	-	260	C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	85	°C/W
Junction-to-Case (Drain)		R _{thJC}	4.3	0/10

Notes

a. Package limited.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

c. When mounted on 1" square PCB (FR4 material).

d. Parametric verification ongoing.

e. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection..

f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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1 For technical questions, contact: automostechsupport@vishay.com

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	75	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2.0	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{V}_{\text{GS}} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 75 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 75 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA
-		$V_{GS} = 0 V$	$V_{DS} = 75 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V _{GS} = 10 V	I _D = 3.8 A	-	0.041	0.050	
Drain-Source On-State Resistance ^a	D D	V _{GS} = 10 V	I _D = 3.8 A, T _J = 125 °C	-	-	0.089	
Drain-Source On-State Resistance	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 3.8 A, T _J = 175 °C	-	-	0.116	Ω
		$V_{GS} = 4.5 V$	I _D = 3.3 A	-	0.055	0.066	1
Forward Transconductanceb	9 _{fs}	V _{DS}	= 15 V, I _D = 3.8 A	-	14	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	630	790	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 35 V, f = 1 MHz	-	84	105	pF
Reverse Transfer Capacitance	C _{rss}			-	36	45	
Total Gate Charge ^c	Qg			-	14	21	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 35 \text{ V}, \text{ I}_{D} = 9.7 \text{ A}$	-	2.3	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	2.9	-	
Gate Resistance	R _g		f = 1 MHz	1.3	2.67	4	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	9	14	
Rise Time ^c	t _r	V _{DD} :	= 35 V, R _L = 35 Ω	-	10	15	ne
Turn-Off Delay Time ^c	t _{d(off)}	I _D ≅ 1 A, '	$V_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$	-	16	24	ns
Fall Time ^c	t _f			-	12	18	1
Source-Drain Diode Ratings and Char	acteristics ^b	·					
Pulsed Current ^a	I _{SM}			-	-	68	Α
Forward Voltage	V _{SD}		= 2.4 A, V _{GS} = 0	-	0.8	1.1	V

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



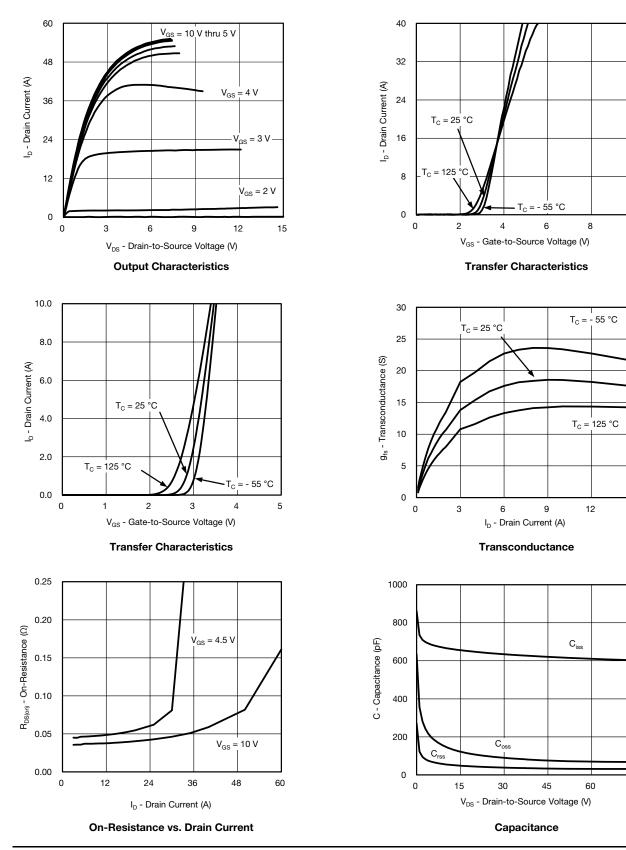
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



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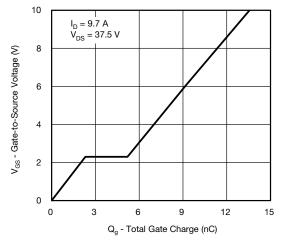
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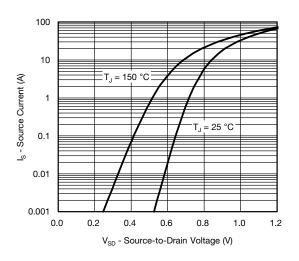
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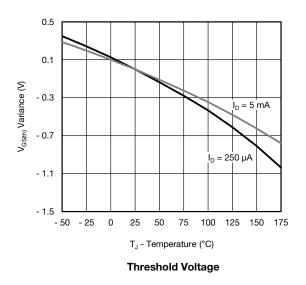
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

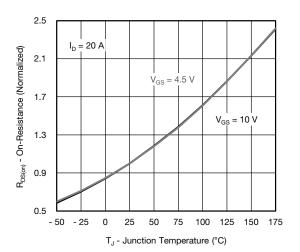




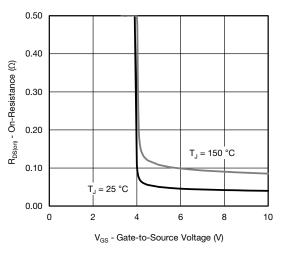


Source Drain Diode Forward Voltage

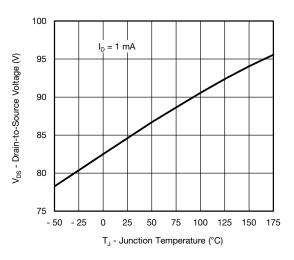




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

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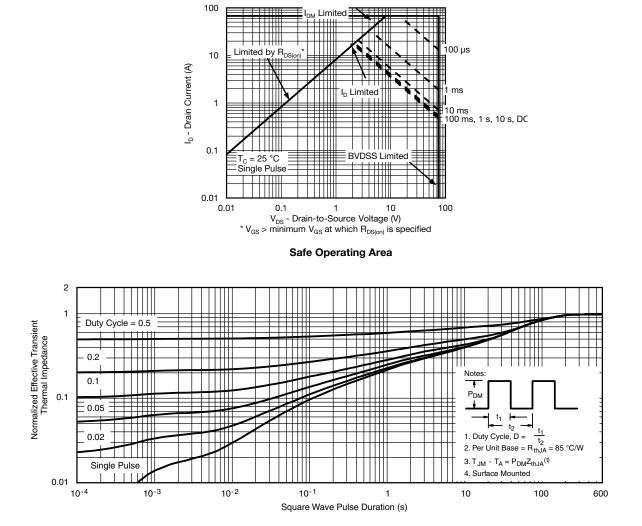
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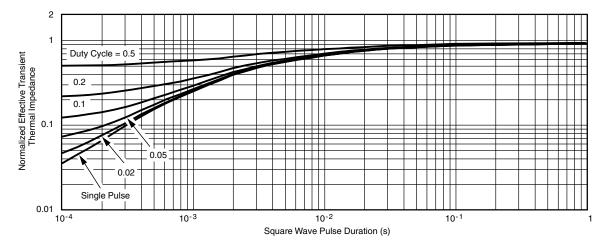
THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

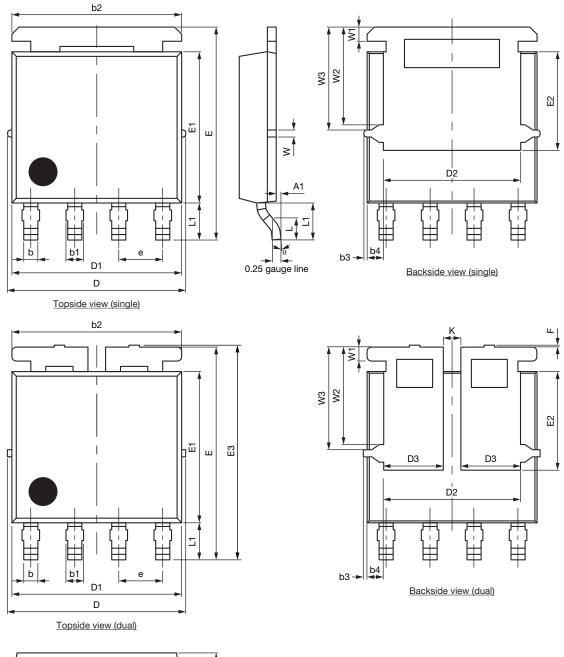
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

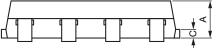
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62833.

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Package Information



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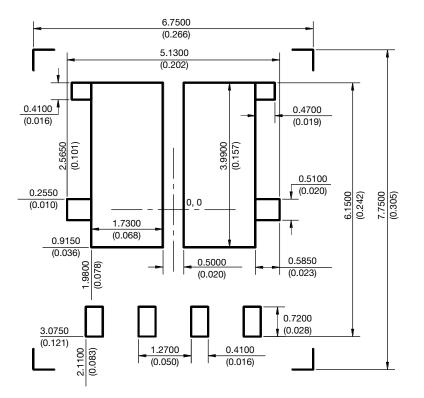
DIM		MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	MIN. NOM.		
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
E3	6.05	6.22	6.40	0.238	0.245	0.252	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51		0.020			
W		0.23		0.009			
W1	0.41		0.016				
W2		2.82		0.111			
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)

Revision: 07-Feb-12



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